

Three Phase Diode Bridge & Thyristor

V_{DRM} / V_{RRM} 800 to 1600V

I_{FAV} / I_{TAV} 200 Amp

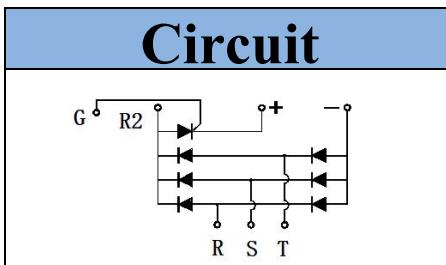
Features

- Aluminum oxide DBC
- Glass passivated chip



Applications

- Inverter for AC or DC motor control
- Current stabilized power supply
- Switching power supply



Module Type

Type	V _{RRM} / V _{DRM}	V _{RSM}
MDST200-08	800V	900V
MDST200-12	1200V	1300V
MDST200-16	1600V	1700V

Diode

■ Maximum Ratings

Symbol	Item	Conditions	Values	Unit
I _D	Output Current	Three Phase, Full Wave T _c = 90°C	200	A
I _{FSM}	Surge Forward Current	t = 10ms T _j = 25°C	2240	A
I ² t	Circuit Fusing Consideration	t = 10ms T _j = 25°C	25088	A ² s
V _{Iso}	Isolation Breakdown Voltage	AC 50Hz; R.M.S; 1min	3000	V
T _j	Operating Junction Temperature		-40 to +150	°C
T _{stg}	Storage Temperature		-40 to +125	°C
M _t	Mounting Torque	To Terminals(M4)	2±15%	N·m
M _s		To Terminals(M6)	5±15%	
Weight		To Heatsink(M6)	5±15%	
			360	g

■ Thermal Characteristics

Symbol	Item	Conditions	Values	Unit
R _{th(j-c)}	Thermal Impedance, Max	Junction to Case(Per Module)	0.12	°C/W
R _{th(c-s)}	Thermal Impedance, Max	Case to Heat Sink	0.05	°C/W

■ Electrical Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
V _{FM}	Forward Voltage Drop, Max	T _j = 25°C I _F = 200A	—	—	1.35	V
I _{RRM}	Repetitive Peak Reverse Current, Max	T _j = 25°C V _R = V _{RRM}	—	—	0.5	mA
		T _j = 150°C V _R = V _{RRM}			10	
V _{TO}	Threshold Voltage, for power loss calculation only	T _j = 125°C		0.80		V
r _T	Slope Resistance, for power loss calculation only	T _j = 125°C		2.25		mΩ

Thyristor

■ Maximum Ratings

Symbol	Item	Conditions	Values	Unit
I _{TAV}	Average On-state Current	T _c = 90°C, Three Phase Full Wave Rectified	200	A
I _{TSM}	Surge On-state Current	T _j = 25°C, t = 50Hz(10ms), V _R = 0V	2400	A
I ² t	Circuit Fusing Consideration		28800	A ² s
V _{Iso}	Isolation Breakdown Voltage	AC 50Hz; R.M.S;1min	3000	V
T _j	Operating Junction Temperature		-40 to + 125	°C
T _{stg}	Storage Temperature		-40 to + 125	°C
di/dt	Critical Rate of Rise of On-state Current, Max	T _j = 125°C, V _D = 1/2V _{DRM} , I _G = 100mA, dI _G /dt = 0.1A/μs	150	A/μs

■ Thermal Characteristics

Symbol	Item	Conditions	Values	Unit
R _{th(j-c)}	Thermal Impedance, Max	Junction to Case	0.14	°C/W
R _{th(c-s)}	Thermal Impedance, Max	Case to Heat Sink	0.05	°C/W

■ Electrical Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
V _{TM}	Peak On-State Voltage, Max	T _j = 25°C, I _T = 200A	-	-	1.30	V
I _{DRM} / _{IRRM}	Repetitive Peak Reverse Current, Max /Repetitive Peak Off-state Current, Max	T _j = 125°C, V _R = V _{RRM} , V _D = V _{DRM}	-	-	30	mA
V _{GT}	Gate Trigger Voltage, Max	T _j = 25°C, V _D = 6V	-	-	3.0	V
I _{GT}	Gate Trigger Current, Max	T _j = 25°C, V _D = 6V	-	-	150	mA
V _{GD}	Gate Non-Trigger Voltage, Max	T _j = 125°C, V _D = 2/3V _{DRM}	-	-	0.25	V
I _L	Latching Current	T _j = 25°C	-	150	-	mA
I _H	Holding Current	T _j = 25°C	-	100	-	mA
t _{gt}	Turn On Time	T _j = 25°C	-	3	-	μs
dv/dt	Critical Rate of Rise of Off-state Voltage, Min	T _j = 125°C, V _D = 2/3V _{DRM} Linear Voltage Rise			500	V/μs
V _{TO}	Threshold Voltage, for power loss calculation only	T _j = 125°C			0.89	V
r _T	Slope Resistance, for power loss calculation only	T _j = 125°C			1.8	mΩ

Performance Curves

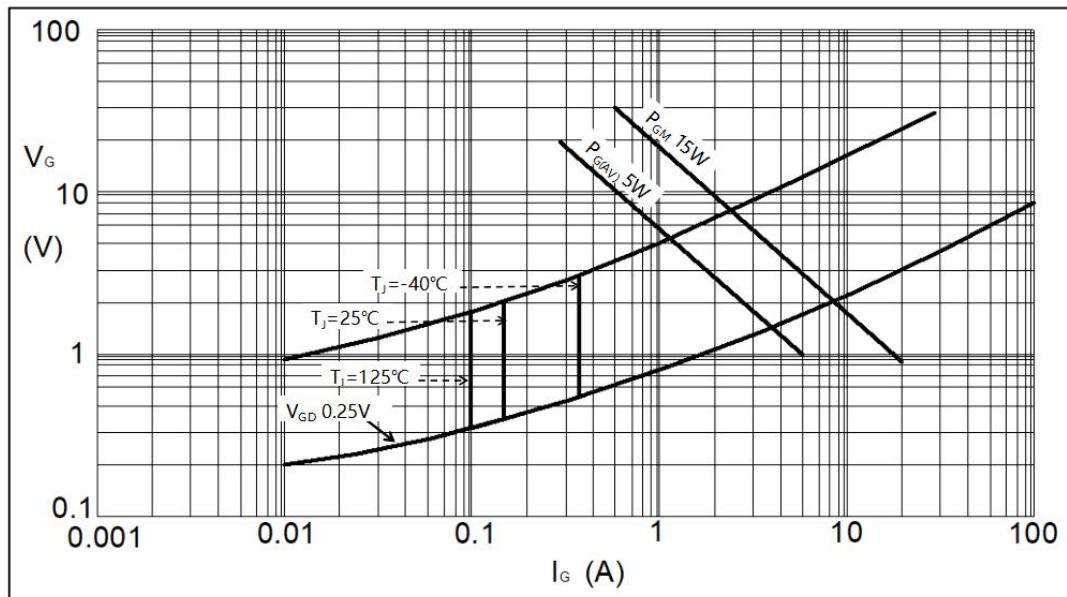


Fig1. Gate Trigger Characteristics

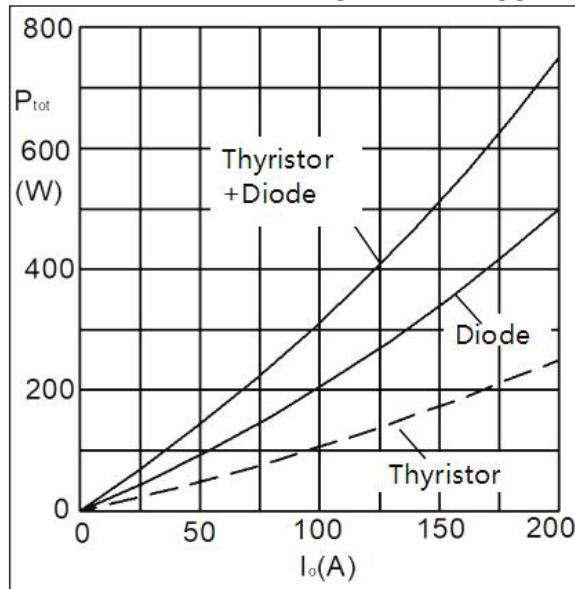


Fig2. Power Dissipation

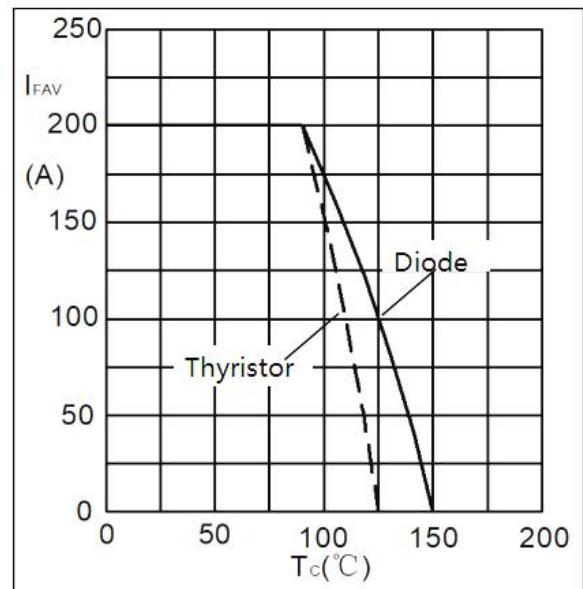


Fig3. Forward Current Derating Curve

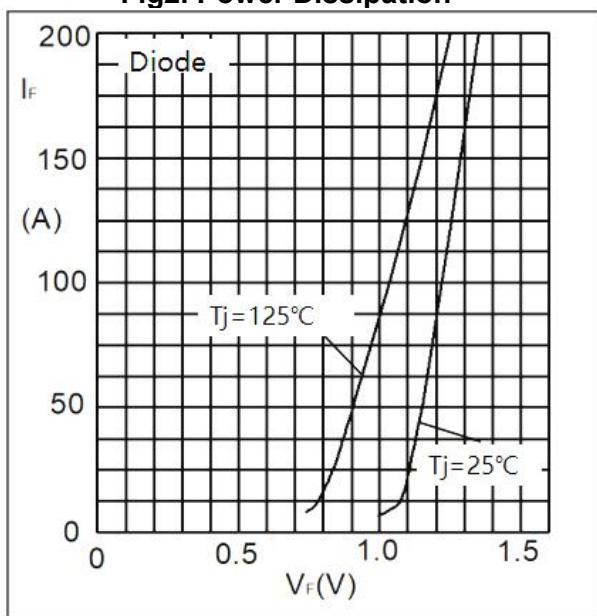
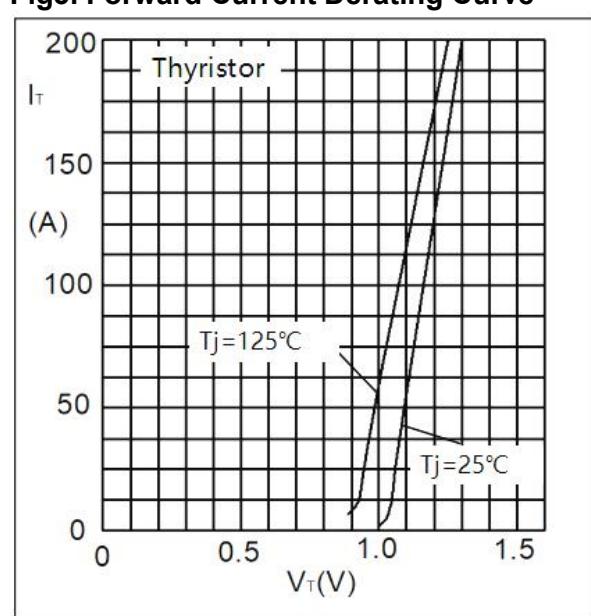


Fig4. Forward Characteristics



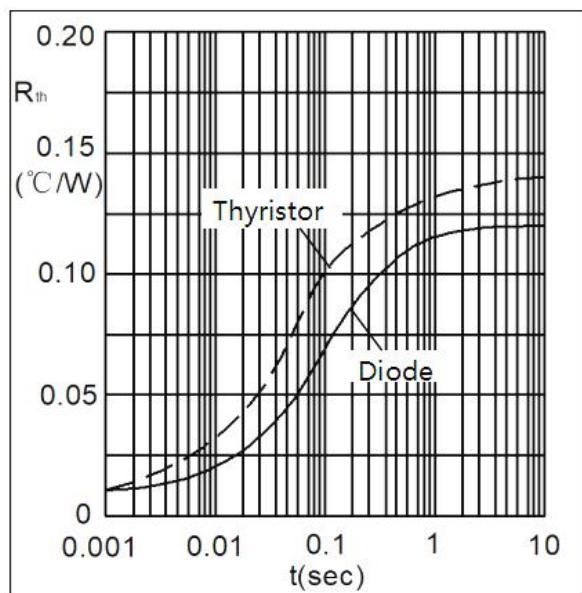


Fig5. Transient Thermal impedance

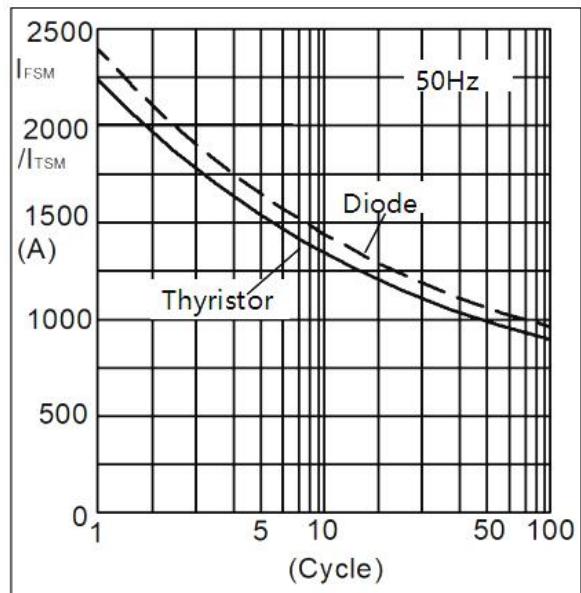
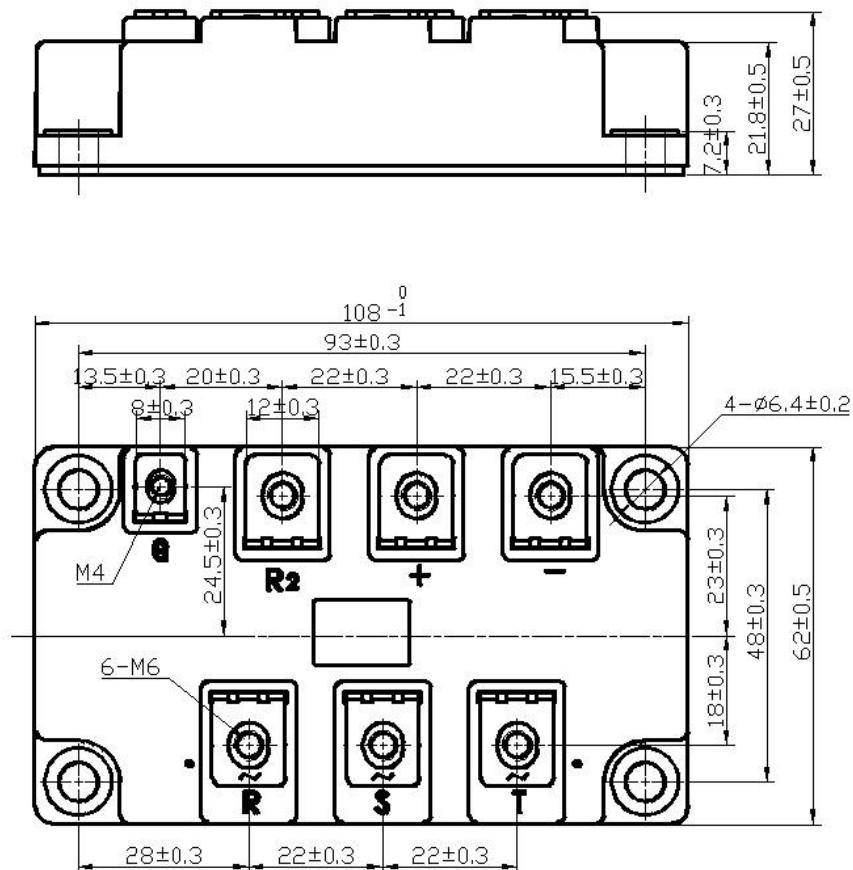


Fig6. Max Non-Repetitive Forward Surge Current

Package Outline Information

CASE: M51B



Dimensions in mm